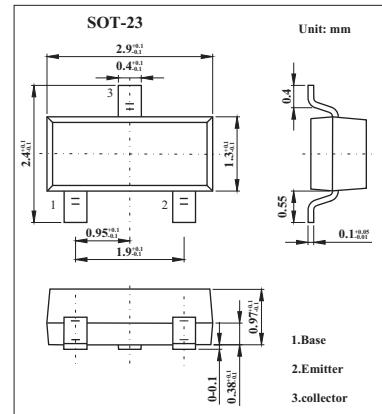


■ Features

- Collector current: $I_C = 2A$
- power dissipation : $P_C = 625mW$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	2	A
Base current	I_B	0.5	A
Power dissipation	P_C	625	mW
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _c =100 μ A	50			V
Collector-emitter breakdown voltage *	V _{CEO}	I _c =10mA	50			V
Emitter-base breakdown voltage	V _{EBO}	I _E =100 μ A	5			V
Collector cutoff current	I _{CBO}	V _{CB} =40V			100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =4V			100	nA
Collector emitter cutoff current	I _{CES}	V _{CES} =40V			100	nA
Collector-emitter saturation voltage *	V _{CES(sat)}	I _c =0.1A, I _B =10mA		10	20	mV
		I _c =1A, I _B =10mA		125	200	mV
		I _c =2A, I _B =50mA		150	220	mV
Base-Emitter Saturation Voltage *	V _{BE(sat)}	I _c =2A, I _B =50mA*		0.87	1.0	V
Base-Emitter Turn-On Voltage *	V _{BE(on)}	I _c =2A, V _{CE} =2V*		0.80	1.0	V
DC current gain	h _{FE}	I _c =10mA, V _{CE} =2V*	200	400		
		I _c =200mA, V _{CE} =2V	300	450		
		I _c =1A, V _{CE} =2V*	200	400		
		I _c =2A, V _{CE} =2V*	100	225		
		I _c =6A, V _{CE} =2V*		40		
Output capacitance	C _{ob}	V _{CB} =10V, f=1MHz		12	20	pF
Transition frequency	f _T	I _c =50mA, V _{CE} =10V, f=100MHz	165			MHz

* Pulse test: tp ≤ 300 μs; d ≤ 0.02.

■ Marking

Marking	619
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